

IN THE CLAIMS

This listing of the claims replaces all prior listings.

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
 - a substrate;
 - a first insulation film formed on the substrate;
 - a first conductive layer formed on the substrate with the first insulation film positioned between the substrate and the first conductive layer;
 - a second conductive layer formed on the substrate at a predetermined distance from the first conductive layer;
 - a diffusion protection film formed on upper surfaces of the first conductive layer, the second conductive layer, and the first insulation film, the diffusion protection film is made of SiC;
 - a second insulation film formed on upper surfaces of the diffusion protection film, the first conductive layer and the second conductive layer and having a plurality of first opening portions to expose either the first conductive layer or the second conductive layer and one or more second opening portions to expose neither the first conductive layer nor the second conductive layer and expose the first insulation film; and
 - a third conductive layer formed on an upper surface of the second insulation film in such a manner to fill up the first opening portions and the second opening portions for making electrical connection between the first conductive layer and the second conductive layer by way of the first opening portions;
- wherein,

the second opening portions are formed between a pair of the first opening portions along the third conductive layer, and

the second insulation film is formed by a low dielectric constant material having a lower Young's modulus than that of a SiO₂ film ~~or a SiO₂ film containing fluorine~~, and

the third opening portions are formed at predetermined distances of about 100 μ m between each other and between the first and second opening portions along the length of the third conductive layer.

2. (Cancelled)

3. (Original) The semiconductor device of claim 1, wherein the third conductive layer is formed by a conductive material containing copper.

4. (Currently Amended) A semiconductor device comprising:

a substrate;

a first insulation film formed on the substrate;

a first conductive layer formed on the substrate with the first insulation film positioned between the substrate and the first conductive layer;

a second conductive layer formed on the substrate at a predetermined distance from the first conductive layer;

a diffusion protection film is formed on upper surfaces of the first conductive layer, the second conductive layer, and the first insulation film, the diffusion protection film is made of Silicon Carbide (SiC);

a second insulation film formed on upper surfaces of the diffusion protection film, the first conductive layer and the second conductive layer and having ~~a plurality of~~ first opening portions to expose one end portion of the first conductive layer, ~~or~~ second opening portions to expose one end portion of the second conductive layer, ~~or~~ and third opening portions to expose a portion of the first insulation film located between the first and second conductive layers; and

a third conductive layer formed on an upper surface of the second insulation film in such a manner to fill up the opening portions for making electrical connection between the first conductive layer and the second conductive layer;

wherein,

the third conductive layer has a predetermined wiring length to maintain the connection even if the length of the third conductive layer in a direction of longer length changes due to thermal expansion or contraction, and has the electrical connection between the first conductive layer and the second conductive layer at both ends of the third conductive layer by way of the first and second opening portions, and

the second insulation film is formed by a low dielectric constant material having a lower Young's modulus than that of a SiO₂ film ~~or a SiO₂ film containing fluorine~~, and

the third opening portions are formed at predetermined distances of about 100 μ m between each other and between the first and second opening portions along the length of the third conductive layer.

5. (Original) The semiconductor device of claim 4, wherein the third conductive layer is formed by a conductive material containing copper.

6. – 7. (Cancelled)